Renesas Electronics America Inc - R5F212A8SNFA#X6 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	55
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212a8snfa-x6

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1. Overview

1.1 Features

The R8C/2A Group and R8C/2B Group of single-chip MCUs incorporates the R8C/Tiny Series CPU core, employing sophisticated instructions for a high level of efficiency. With 1 Mbyte of address space, and it is capable of executing instructions at high speed. In addition, the CPU core boasts a multiplier for high-speed operation processing.
Power consumption is low, and the supported operating modes allow additional power control. These MCUs also use an anti-noise configuration to reduce emissions of electromagnetic noise and are designed to withstand EMI.
Integration of many peripheral functions, including multifunction timer and serial interface, reduces the number of system components.
Furthermore, the R8C/2B Group has on-chip data flash (1 KB × 2 blocks).
The difference between the R8C/2A Group and R8C/2B Group is only the presence or absence of data flash. Their peripheral functions are the same.

1.1.1 Applications

Electronic household appliances, office equipment, audio equipment, consumer equipment, etc.

Table 1.2 Specifications for R8C/2A Group (2)

Item	Function	Specification
Serial Interface	UART0, UART1, UART2	Clock synchronous serial I/O/UART × 3
Clock Synchronous Serial I/O with Chip Select (SSU)		1 (shared with I2C-bus)
I2C bus(1)		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function
D/A Converter		8-bit resolution × 2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 100 times • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 3.0 to 5.5 V) f(XIN) = 10 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 2.2 to 5.5 V)
Current consumption		12 mA (VCC = 5.0 V, f(XIN) = 20 MHz) 5.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) 2.1 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) 0.65 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version)(2) -20 to 105°C (Y version)(3)
Package		64-pin LQFP • Package code: PLQP0064KB-A (previous code: 64P6Q-A) • Package code: PLQP0064GA-A (previous code: 64P6U-A) 64-pin FLGA • Package code: PTLG0064JA-A (previous code: 64F0G)

NOTES:
1. I2C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D version if D version functions are to be used.
3. Please contact Renesas Technology sales offices for the Y version.

1.3 Block Diagram

Figure 1.3 shows a Block Diagram.

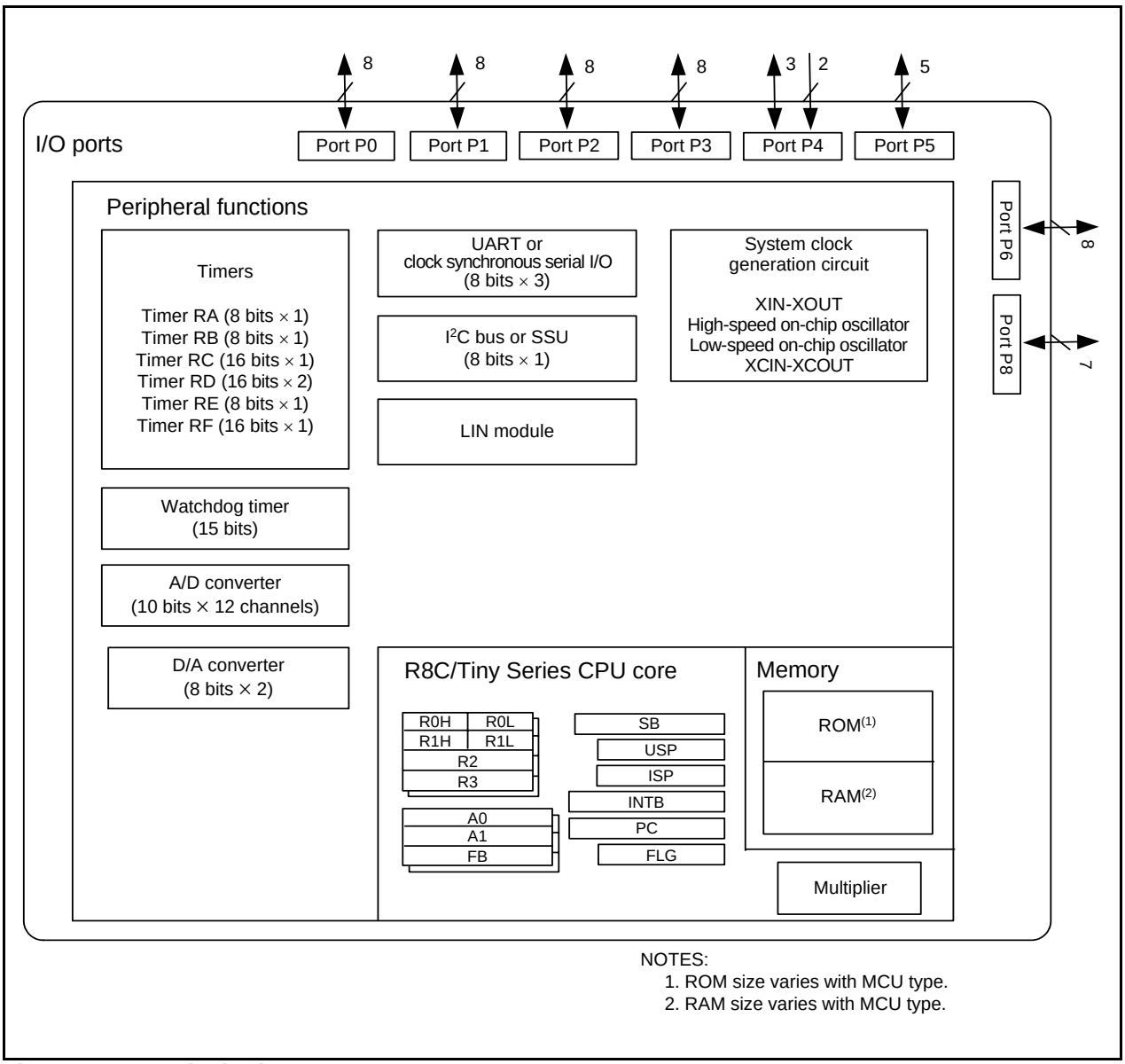


Figure 1.3 Block Diagram

Table 1.10 Pin Functions (2)

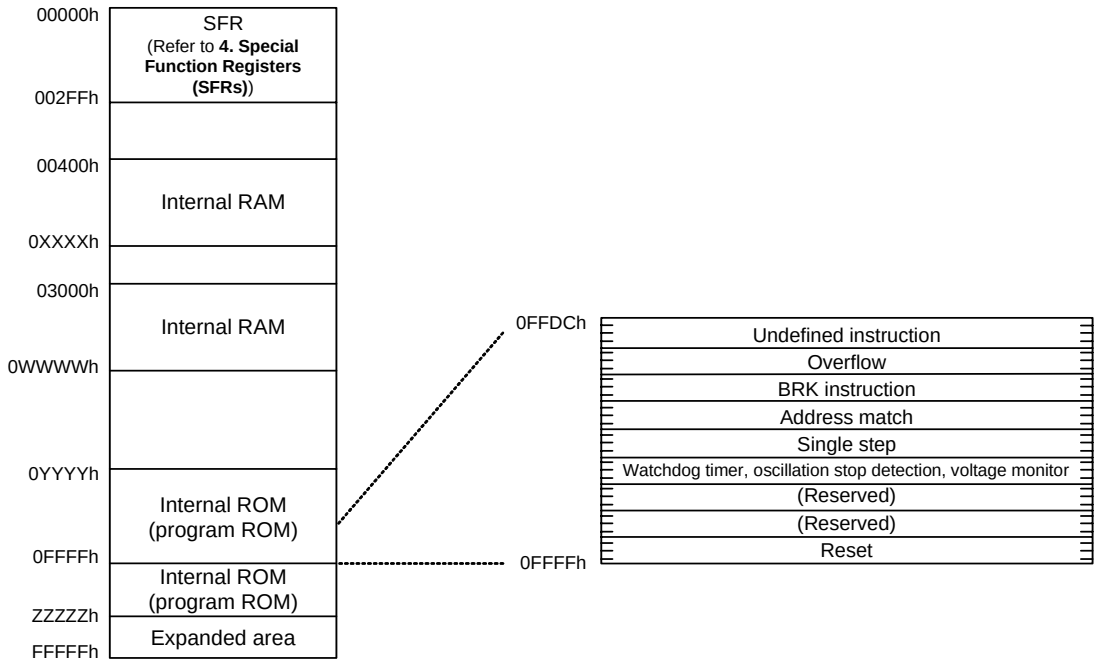
Item	Pin Name	I/O Type	Description
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
D/A converter	DA0 to DA1	O	D/A converter output pins
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_5, P5_0 to P5_4, P6_0 to P6_7, P8_0 to P8_6	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P2_0 to P2_7 also function as LED drive ports.
Input port	P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

3. Memory

3.1 R8C/2A Group

Figure 3.1 is a Memory Map of R8C/2A Group. The R8C/2A group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



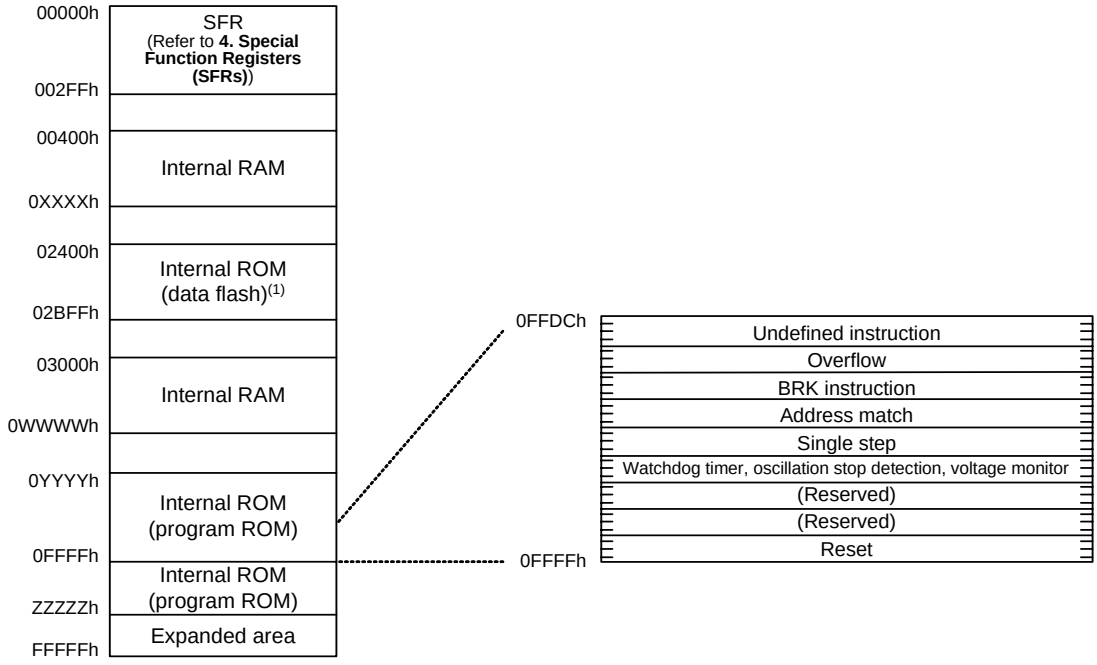
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Internal ROM			Internal RAM		
Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0WWWWh
48 Kbytes	04000h	–	2.5 Kbytes	00DFFh	–
64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	–
96 Kbytes	04000h	1BFFFh	7 Kbytes	011FFh	03DFFh
128 Kbytes	04000h	23FFFh	7.5 Kbytes	011FFh	03FFFh

Figure 3.1 Memory Map of R8C/2A Group

3.2 R8C/2B Group

Figure 3.2 is a Memory Map of R8C/2B Group. The R8C/2B group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Internal ROM			Internal RAM		
Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0WWWWh
48 Kbytes	04000h	–	2.5 Kbytes	00DFFh	–
64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	–
96 Kbytes	04000h	1BFFFh	7 Kbytes	011FFh	03DFFh
128 Kbytes	04000h	23FFFh	7.5 Kbytes	011FFh	03FFFh

Figure 3.2 Memory Map of R8C/2B Group

Table 4.4 SFR Information (4)(1)

Address	Register	Symbol	After reset
00C0h			
00C1h			
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h			
00D5h			
00D6h			
00D7h			
00D8h	D/A Register 0	DA0	00h
00D9h			
00DAh	D/A Register 1	DA1	00h
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h	Port P5 Register	P5	XXh
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh	Port P6 Register	P6	XXh
00EDh			
00EEh	Port P6 Direction Register	PD6	00h
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h	Port P2 Drive Capacity Control Register	P2DRR	00h
00F5h	UART1 Function Select Register	U1SR	000000XXb
00F6h			
00F7h			
00F8h	Port Mode Register	PMR	00h
00F9h	External Input Enable Register	INTEN	00h
00FAh	INT Input Filter Select Register	INTF	00h
00FBh	Key Input Enable Register	KIEN	00h
00FCh	Pull-Up Control Register 0	PUR0	00h
00FDh	Pull-Up Control Register 1	PUR1	XX000000b
00FEh			
00FFh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.11 SFR Information (11)[1]

Address	Register	Symbol	After reset
0280h			
0281h			
0282h			
0283h			
0284h			
0285h			
0286h			
0287h			
0288h			
0289h			
028Ah			
028Bh			
028Ch			
028Dh			
028Eh			
028Fh			
0290h	Timer RF Register	TRF	00h
0291h			00h
0292h			
0293h			
0294h			
0295h			
0296h			
0297h			
0298h			
0299h			
029Ah	Timer RF Control Register 0	TRFCR0	00h
029Bh	Timer RF Control Register 1	TRFCR1	00h
029Ch	Capture / Compare 0 Register	TRFM0	0000h[2]
029Dh			FFFFh[3]
029Eh	Compare 1 Register	TRFM1	FFh
029Fh			FFh
02A0h			
02A1h			
02A2h			
02A3h			
02A4h			
02A5h			
02A6h			
02A7h			
02A8h			
02A9h			
02AAh			
02ABh			
02ACh			
02ADh			
02AEh			
02AFh			
02B0h			
02B1h			
02B2h			
02B3h			
02B4h			
02B5h			
02B6h			
02B7h			
02B8h			
02B9h			
02BAh			
02BBh			
02BCh			
02BDh			
02BEh			
02BFh			

NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. After input capture mode.
3. After output compare mode.

Table 4.12 SFR Information (12)(1)

Address	Register	Symbol	After reset
02C0h	A/D Register 0	AD0	XXh
02C1h			XXh
02C2h			
02C3h			
02C4h			
02C5h			
02C6h			
02C7h			
02C8h			
02C9h			
02CAh			
02CBh			
02CCh			
02CDh			
02CEh			
02CFh			
02D0h			
02D1h			
02D2h			
02D3h			
02D4h	A/D Control Register 2	ADCON2	00001000b
02D5h			
02D6h	A/D Control Register 0	ADCON0	00000011b
02D7h	A/D Control Register 1	ADCON1	00h
02D8h			
02D9h			
02DAh			
02DBh			
02DCh			
02DDh			
02DEh			
02DFh			
02E0h			
02E1h			
02E2h			
02E3h			
02E4h	Port P8 Direction Register	PD8	00h
02E5h			
02E6h	Port P8 Register	P8	XXh
02E7h			
02E8h			
02E9h			
02EAh			
02EBh			
02ECh			
02EDh			
02EEh			
02EFh			
02F0h			
02F1h			
02F2h			
02F3h			
02F4h			
02F5h			
02F6h			
02F7h			
02F8h			
02F9h			
02FAh			
02FBh			
02FCh	Pull-Up Control Register 2	PUR2	XXX00000b
02FDh			
02FEh			
02FFh	Timer RF Output Control Register	TRFOUT	00h
FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

Table 5.5 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/2A Group	100(3)	–	–	times
		R8C/2B Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

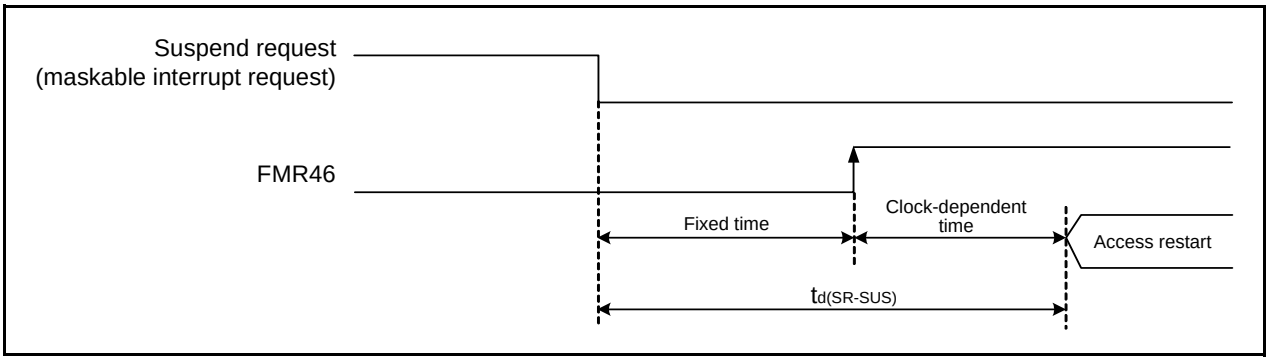


Figure 5.2 Time delay until Suspend

Table 5.7 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 V to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.8 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 V to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.9 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 V to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

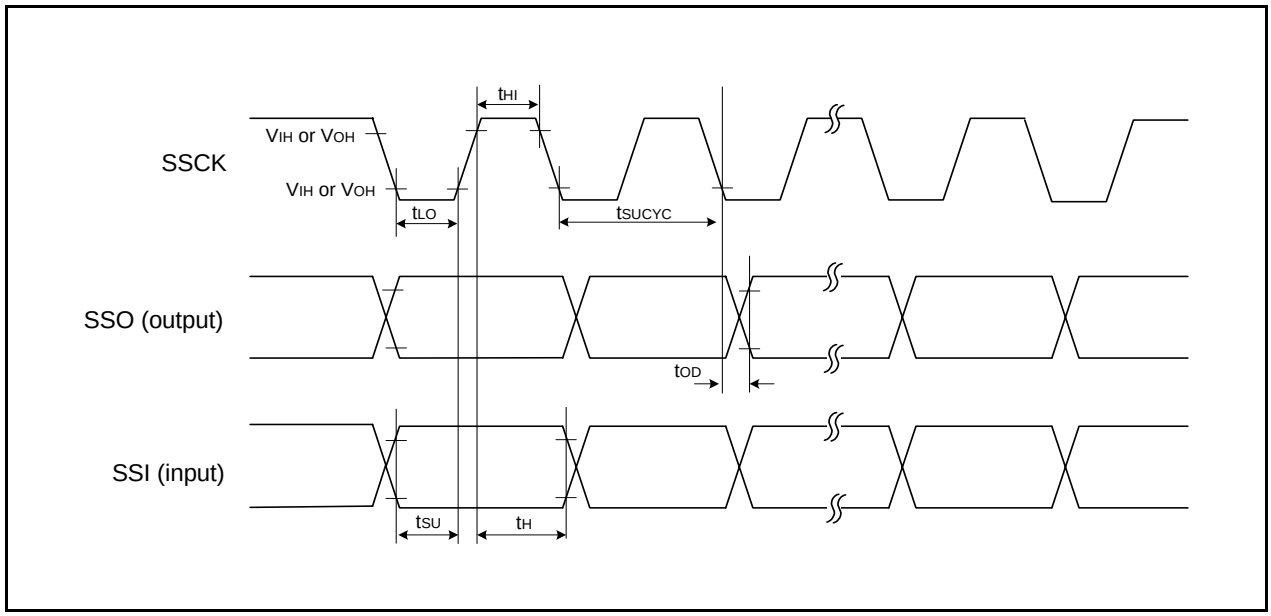
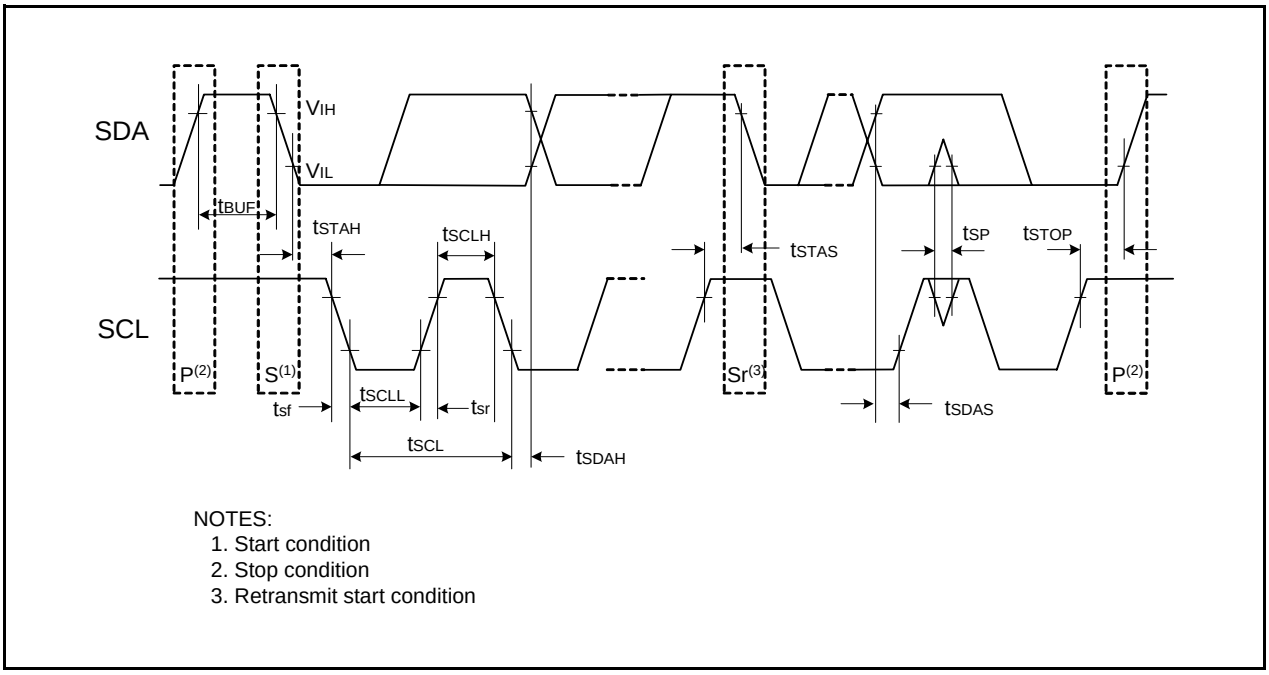


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.15 Timing Requirements of I²C bus Interface (1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600^{(2)}$	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300^{(2)}$	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500^{(2)}$	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}^{(2)}$	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}^{(2)}$	–	–	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}^{(2)}$	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}^{(2)}$	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}^{(2)}$	–	–	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 20^{(2)}$	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$



NOTES:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.7 I/O Timing of I²C bus Interface

Table 5.16 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = -5 mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = -200 µA		V_{CC} – 0.5	–	V_{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = -20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -5 mA	V_{CC} – 2.0	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 µA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 µA		–	–	0.45	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, KI0, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	-5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.23 Electrical Characteristics (3) [Vcc = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = -1 mA		Vcc – 0.5	–	Vcc	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = -5 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -1 mA	Vcc – 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -50 µA	Vcc – 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. Vcc =2.7 to 3.3 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.28 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width	150	–	ns
$t_{W(CKL)}$	CLKi Input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 to 2

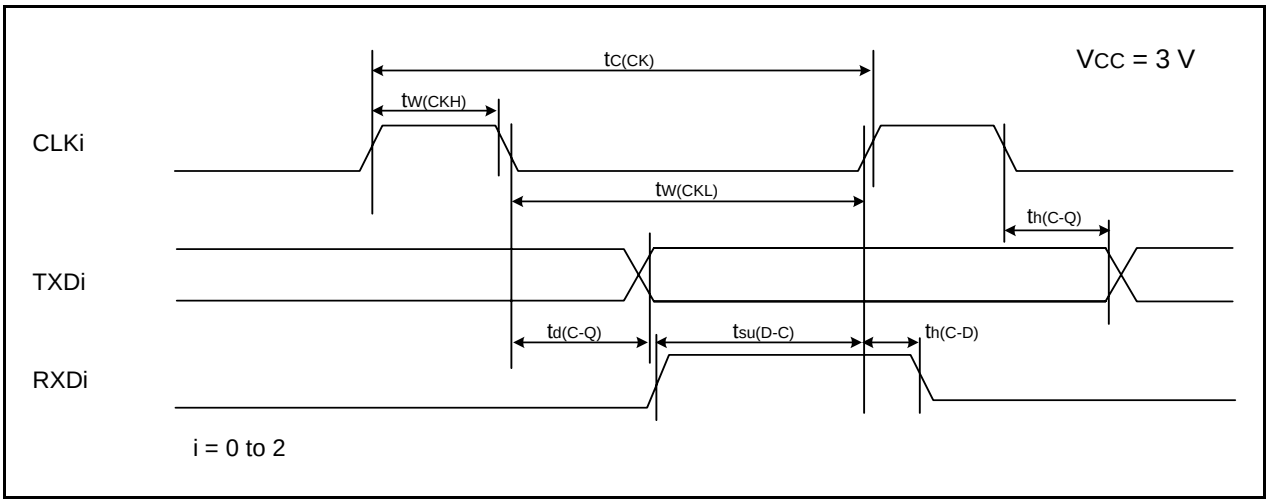


Figure 5.16 Serial Interface Timing Diagram when VCC = 3 V

Table 5.29 External Interrupt $\overline{INTi}$ (i = 0, 2, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INT0}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{INT0}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

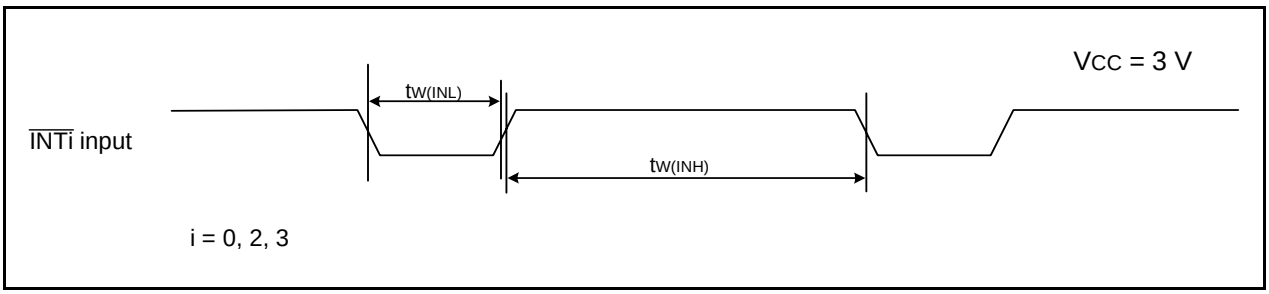


Figure 5.17 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 3 V

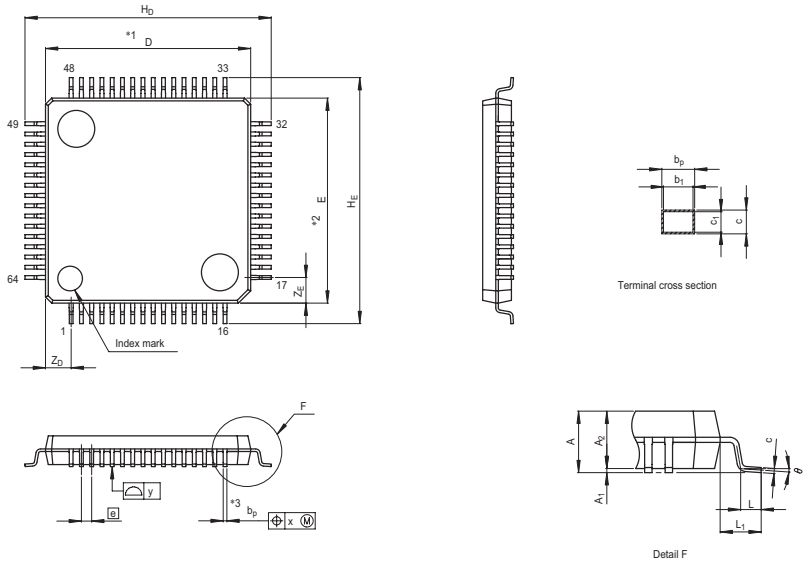
Table 5.31 Electrical Characteristics (6) [Vcc = 2.2 V]
(Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	110	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	125	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	27	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	12	40	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.8	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.9	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.6	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.60	–	µA

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

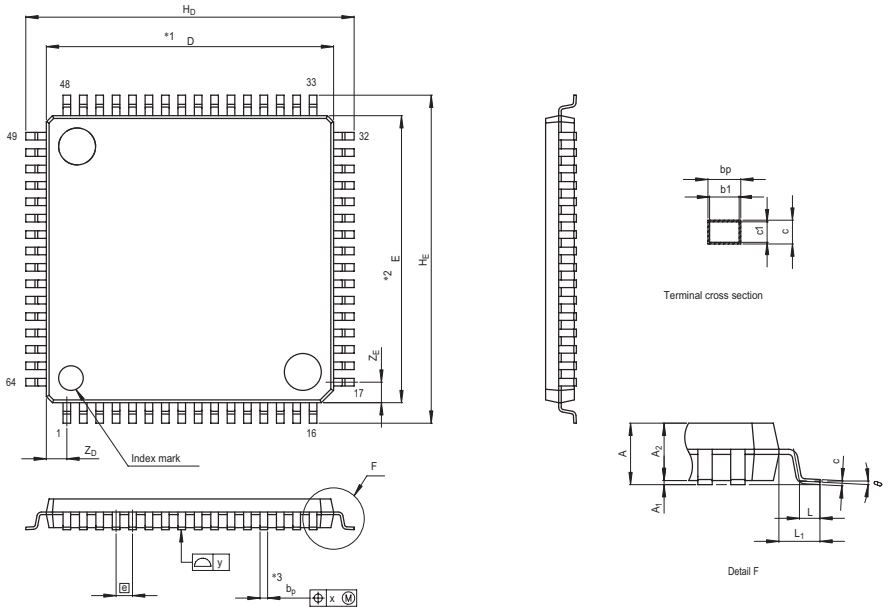
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP64-10x10-0.50	PLQP0064KB-A	64P6Q-A / FP-64K / FP-64KV	0.3g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP64-14x14-0.80	PLQP0064GA-A	64P6U-A	0.7g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.32	0.37	0.42
b_1	—	0.35	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.8	—
x	—	—	0.20
y	—	—	0.10
Z_D	—	1.0	—
Z_E	—	1.0	—
L	0.3	0.5	0.7
L_1	—	1.0	—

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

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